

| L Number | Hits | Search Text   | DB  | Time stamp       |
|----------|------|---|---|------------------|
| 1        | 7369 | ((((silicon near on insulator) (SOI)))<br>and ((silicon near oxide) (sio."sub.2")))<br>and (silicon near (substrate base pad<br>wafer))) and (silicon near layer)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/05 16:23 |
| 2        | 1793 | ((((((silicon near on insulator) (SOI)))<br>and ((silicon near oxide) (sio."sub.2")))<br>and (silicon near (substrate base pad<br>wafer))) and (silicon near layer)) and<br>((refractory near metal) (titanium near<br>tungsten) (titanium near nitride)) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/05 16:25 |

| L Number | Hits   | Search Text  | DB  | Time stamp       |
|----------|--------|--|---|------------------|
| 49       | 220768 | ((silicon near on insulator) (SOI))  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/05 13:22 |
| 50       | 25450  | ((silicon near on insulator) (SOI))) and<br>((silicon near oxide) (sio."sub.2"))   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/05 13:23 |
| 51       | 12751  | ((silicon near on insulator) (SOI))) and<br>((silicon near oxide) (sio."sub.2")) and<br>(silicon near (substrate base pad wafer))  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/05 13:24 |
| 53       | 7369   | ((silicon near on insulator) (SOI)))<br>and ((silicon near oxide) (sio."sub.2"))<br>and (silicon near (substrate base pad<br>wafer))) and (silicon near layer)                                 | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/05 13:32 |
| 54       | 904    | ((silicon near on insulator) (SOI)))<br>and ((silicon near oxide) (sio."sub.2"))<br>and (silicon near (substrate base pad<br>wafer))) and (silicon near layer)) and<br>(refractory near metal) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2002/11/05 13:33 |